

50 V, 3 A PNP low VCEsat transistor

10 May 2022

#### 1. General description

PNP low  $V_{\mbox{CEsat}}$  transistor in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package.

NPN complement: PBSS4350T-Q

### 2. Features and benefits

- Low collector-emitter saturation voltage V<sub>CEsat</sub> and corresponding low R<sub>CEsat</sub>
- High collector current capability
- High collector current gain
- Improved efficiency due to reduced heat generation
- · Qualified according to AEC-Q101 and recommended for use in automotive applications

### 3. Applications

- Power management applications
- · Low and medium power DC/DC converters
- Supply line switching
- Battery chargers
- Linear voltage regulation with low voltage drop-out (LDO)

### 4. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>CEO</sub>	collector-emitter voltage	open base	-	-	-50	V
I <sub>C</sub>	collector current		-	-	-2	А
I <sub>CRM</sub>		$\delta \le 0.25$ ; Operated under pulsed conditions; $t_p \le 100$ ms	-	-	-3	A
R <sub>CEsat</sub>	collector-emitter saturation resistance	I <sub>C</sub> = -2 A; I <sub>B</sub> = -200 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	90	135	mΩ

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### 5. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	3	
2	E	emitter		С
3	С	collector		B

### 6. Ordering information

#### Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PBSS5350T-Q	SOT23	plastic, surface-mounted package; 3 terminals; 1.9 mm pitch; 2.9 mm x 1.3 mm x 1 mm body	SOT23		

### 7. Marking

#### Table 4. Marking codes

Type number	Marking code[1]
PBSS5350T-Q	ZD%

[1] % = placeholder for manufacturing site code

### 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>CBO</sub>	collector-base voltage	open emitter		-	-50	V
V <sub>CEO</sub>	collector-emitter voltage	open base		-	-50	V
V <sub>EBO</sub>	emitter-base voltage	open collector		-	-5	V
I <sub>C</sub>	collector current			-	-2	А
I <sub>CRM</sub>	repetitive peak collector current	$\delta \le 0.25$ ; Operated under pulsed conditions; $t_p \le 100$ ms		-	-3	A
I <sub>CM</sub>	peak collector current	single pulse; t <sub>p</sub> ≤ 1 ms		-	-5	А
I <sub>B</sub>	base current			-	-0.5	A
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C	[1]	-	300	mW
			[2]	-	480	mW
			[3]	-	540	mW
			[4]	-	500	mW
			[1] [5]	-	1.2	W
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-65	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.

[4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.

[5] Operated under pulsed conditions: pulse width tp  $\leq$  100 ms; duty cycle  $\delta \leq$  0.25.

### 9. Thermal characteristics

Table 6. The	rmal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	rmal resistance from in free air [1] [2] [3] [4] [1][5]	[1]	-	-	417	K/W
			[2]	-	-	260	K/W
			[3]	-	-	230	K/W
			[4]	-	-	250	K/W
			-	-	104	K/W	
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	75	-	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm<sup>2</sup>.

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm<sup>2</sup>.

[4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.

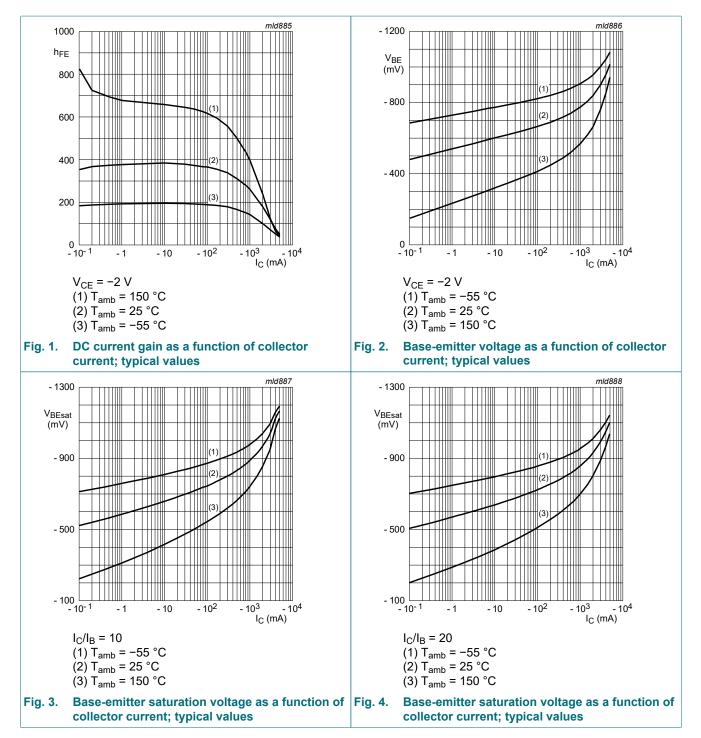
[5] Operated under pulsed conditions: pulse width  $t_p \le 100$  ms; duty cycle  $\delta \le 0.25$ 

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### **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
V <sub>(BR)CBO</sub>	collector-base breakdown voltage	$I_{C}$ = -100 µA; $I_{E}$ = 0 A; $T_{amb}$ = 25 °C	-50	-	-	V
V <sub>(BR)CEO</sub>	collector-emitter breakdown voltage	I <sub>C</sub> = -10 mA; I <sub>B</sub> = 0 A; T <sub>amb</sub> = 25 °C	-50	-	-	V
V <sub>(BR)EBO</sub>	emitter-base breakdown voltage (collector open)	I <sub>E</sub> = -100 μA; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-6	-	-	V
I <sub>сво</sub>	collector-base cut-off	V <sub>CB</sub> = -50 V; I <sub>E</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
	current	V <sub>CB</sub> = -50 V; I <sub>E</sub> = 0 A; T <sub>j</sub> = 150 °C	-	-	-50	μA
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = -5 V; I <sub>C</sub> = 0 A; T <sub>amb</sub> = 25 °C	-	-	-100	nA
h <sub>FE</sub>	DC current gain	$V_{CE}$ = -2 V; I <sub>C</sub> = -100 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	200	-	-	
		$V_{CE}$ = -2 V; I <sub>C</sub> = -500 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	200	-	-	
		$V_{CE}$ = -2 V; I <sub>C</sub> = -1 A; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	200	-	-	
		$V_{CE}$ = -2 V; I <sub>C</sub> = -2 A; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	130	-	-	
		V <sub>CE</sub> = -2 V; I <sub>C</sub> = -3 A; pulsed; t <sub>p</sub> ≤ 300 µs; T <sub>amb</sub> = 25 °C	80	-	-	
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_{C}$ = -500 mA; $I_{B}$ = -50 mA; pulsed; $t_{p}$ ≤ 300 μs; δ = 0.02; $T_{amb}$ = 25 °C	-	-	-90	mV
		I <sub>C</sub> = -1 A; I <sub>B</sub> = -50 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	-	-180	mV
		$I_{C}$ = -2 A; $I_{B}$ = -100 mA; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-	-320	mV
		$I_{C}$ = -2 A; $I_{B}$ = -200 mA; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-	-270	mV
		$I_{C}$ = -3 A; $I_{B}$ = -300 mA; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-	-390	mV
R <sub>CEsat</sub>	collector-emitter saturation resistance	$I_{C}$ = -2 A; $I_{B}$ = -200 mA; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	90	135	mΩ
V <sub>BEsat</sub>	base-emitter saturation voltage	$I_{C}$ = -2 A; $I_{B}$ = -100 mA; pulsed; $t_{p}$ ≤ 300 μs; δ ≤ 0.02; $T_{amb}$ = 25 °C	-	-	-1.1	V
		I <sub>C</sub> = -3 A; I <sub>B</sub> = -300 mA; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	-	-1.2	V
V <sub>BEon</sub>	base-emitter turn-on voltage	$V_{CE}$ = -2 V; I <sub>C</sub> = -1 A; pulsed; t <sub>p</sub> ≤ 300 μs; δ ≤ 0.02; T <sub>amb</sub> = 25 °C	-	-	-1.2	V
fT	transition frequency	V <sub>CE</sub> = -5 V; I <sub>C</sub> = -100 mA; f = 100 MHz; T <sub>amb</sub> = 25 °C	100	-	-	MHz
C <sub>c</sub>	collector capacitance	V <sub>CB</sub> = -10 V; I <sub>E</sub> = 0 A; i <sub>e</sub> = 0 A; f = 1 MHz; T <sub>amb</sub> = 25 °C	-	-	35	pF

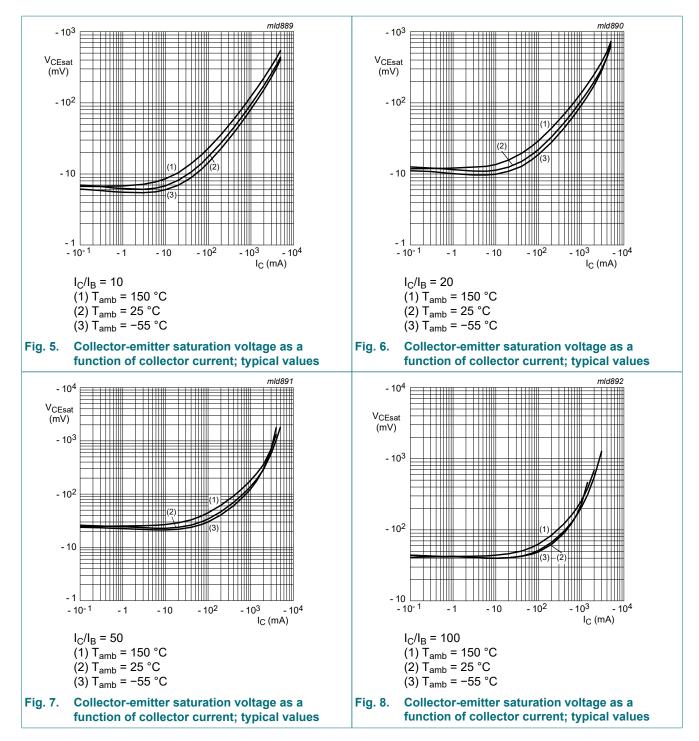
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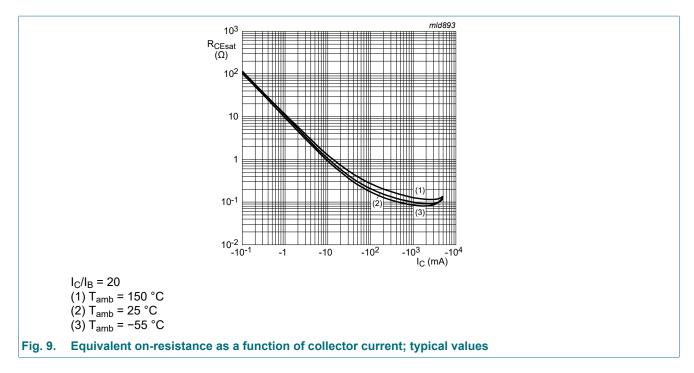


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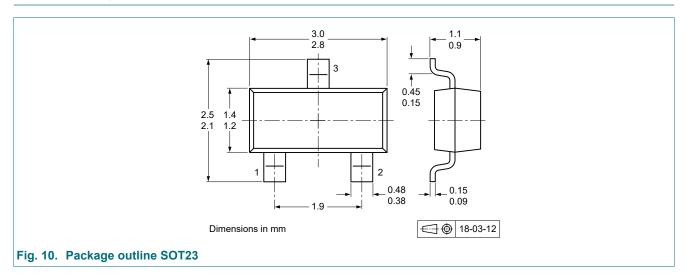


#### 11. Test information

#### **Quality information**

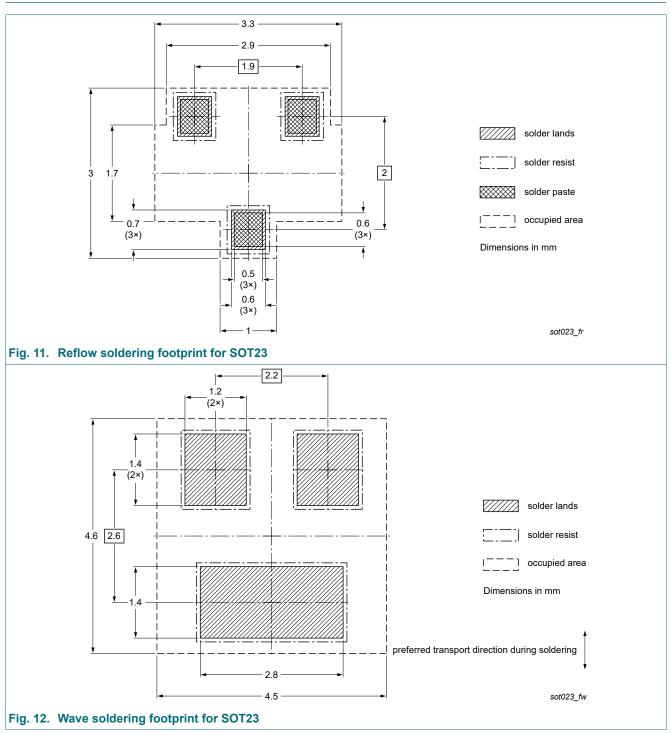
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

#### 12. Package outline



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### 13. Soldering



#### 50 V, 3 A PNP low VCEsat transistor

### 14. Revision history

Table 8. Revision history						
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PBSS5350T-Q v.1	20220510	Product data sheet	-	-		

### 15. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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